NAURA AKRION

HSE M200 PLASMA ETCH SYSTEM

System Overview

HSE M200 Plasma Etch System is designed specifically for deep silicon etching of MEMS and TSV applications. The dual zone RF source creates higher plasma density for higher etch rates. The platform can be configured with up to three process modules for R&D, pilot line, or mass production.

Substrate Size: 200 mm
Applications compounds: Silicon, SOI, SOG
Technology Markets: MEMS, R&D, Advanced Packaging

Processes

- Deep via etch
- Deep trench etch
- SOI etch
- SOG etch

Production Advantages

- Dual RF and gas inlet zones enable optimization of etch uniformity and selectivity
- Fast response gas delivery design minimizes scalloped edges
- Low frequency pulsing reduces positive charge buildup and bottom notch formation
- Provides high aspect ratio etch—up to 70:1

HSE M200 Plasma Etch System

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